ETR0203_004

Low Voltage Detectors (V_{DF} = 0.8V \sim 1.5V) Standard Voltage Detectors (V_{DF} 1.6V \sim 6.0V)

■GENERAL DESCRIPTION

The XC61G series are highly precise, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies.

Detect voltage is extremely accurate with minimal temperature drift.

Both CMOS and N-ch open drain output configurations are available.

■APPLICATIONS

- Microprocessor reset circuitry
- Memory battery back-up circuits
- Power-on reset circuits
- Power failure detection
- System battery life and charge voltage monitors

■ FEATURES

Highly Accurate : ±2%

Low Power Consumption: 0.7 μ A [VIN=1.5V] (TYP.) **Detect Voltage Range** : 0.8V ~ 1.5V in 0.1V increments (Low Voltage)

: 1.6V~6.0V in 0.1V

increments (Standard Voltage)

Operating Voltage Range : 0.7V ~ 6.0V (Low Voltage)

: 0.7V~10.0V (Standard Voltage)

Detect Voltage Temperature characteristics

 ± 100 ppm/°C (TYP.)

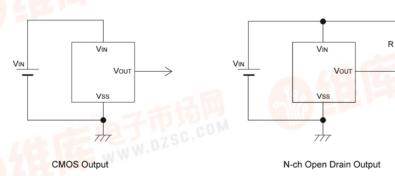
Output Configuration : N-ch open drain output or CMOS

CMOS

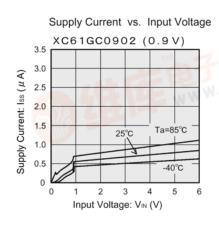
Package : USP-3

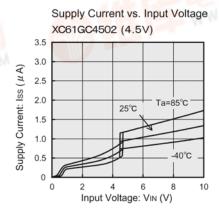
Environmentally Friendly: EU RoHS Compliant, Pb Free

■TYPICAL APPLICATION CIRCUITS



■TYPICAL PERFORMANCE CHARACTERISTICS

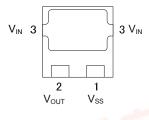






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■PIN CONFIGURATION



(BOTTOM VIEW)

■PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION		
USP-3	FIN NAIVIL	PONCTION		
3	Vin	Supply Voltage		
1	Vss	Ground		
2	Vout	Output		

■PRODUCT CLASSIFICATION

Ordering Information

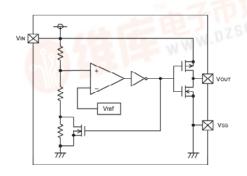
XC61G 1234567-8 (*1)

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
1	Output Configuration	C	CMOS output
	Output Configuration	N	N-ch open drain output
23	Detect Voltage	08 ~ 60	e.g. 0.8V → ②0, ③8
23	Detect voltage		e.g. 1.5V → ②1, ③5
4	Output Delay	0	No delay
(5)	Detect Accuracy	2	Within ± 2%
67-8	Packages	HR	USP-3 (3,000/Reel)
	(Oder Unit)	HR-G	USP-3 (3,000/Reel)

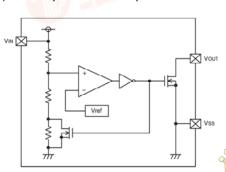
The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

■BLOCK DIAGRAMS

(1) CMOS Output



(2) N-ch Open Drain Output



■ ABSOLUTE MAXIMUM RATINGS

Ta = 25°C

PARAMETER			SYMBOL	RATINGS	UNITS	
Input Voltage *1 *2		*1	Vin	V _{SS} -0.3 ~ 9.0	V	
		*2	VIIN	V _{SS} -0.3 ~ 12.0	n756.60	
0.15.10.55.1		*1	lout	50	A	
Output Cu	Output Current		lout	50	- mA	
	CMOS		Vouт	Vss -0.3 ~ Vin +0.3		
Output Voltage	N-ch Open Drain Output *1 N-ch Open Drain Output *2			Vss -0.3 ~ 9.0	V	
				Vss -0.3 ~ 12.0		
Power Dissipation	USP-3		Pd	120	mW	
Operating Temperature Range		Topr	-40 ~ +85	°C		
Storage Temperature Range		Tstg	-40~+125 	°C		

■ELECTRICAL CHARACTERISTICS

 $VDF(T) = 0.8 \text{ to } 6.0V \pm 2\%$

Ta=25°C

PARAN	METER	SYMBOL	CONDITION	IS	MIN.	TYP.	MAX.	UNITS	CIRCUITS	
Detect	Voltage	VDF			V _{DF} x 0.98	V_{DF}	V _{DF} x 1.02	V	0M ₁	
Hysteres	is Range	VHYS	-1217		V _{DF} x 0.02	V _{DF} x 0.05	V _{DF} x 0.08	V	1	
			V _{IN} = 1.5V		-	0.7	2.3			
		二吧.	V _{IN} = 2.0V		-	0.8	2.7			
Supply	Current	Iss	$V_{IN} = 3.0V$,	-	0.9	3.0	μΑ	2	
00			$V_{IN} = 4.0V$,	-	1.0	3.2			
			$V_{IN} = 5.0V$	•	-	1.1	3.6	1	M	
Operating	g Voltage	V _{IN}	$V_{DF(T)} = 0.8V \text{ to}$	1.5V	0.7	- 103	6.0	V	1	
Орстанту	y voltage	VIN	$V_{DF(T)} = 1.6V \text{ to}$	$V_{DF(T)} = 1.6V \text{ to } 6.0V$			10.0	7.C.C.	OM1	
O. day of O. anno at		N ab 1/ - 0.5	N-ch, V _{DS} = 0.5V -	$V_{IN} = 0.7V$	0.10	0.80	1.W-W.1	L	3	
	Output Current		N-cn, V _{DS} = 0.5V -	$V_{IN} = 1.0V$	0.85	2.70	-			
(Low Voltage)			CMOS, P-ch, V _{DS} =2.1V	V _{IN} =6.0V		-7.5	-1.5		4	
- #3h (三世.	V.DZSC.COM	V _{IN} =1.0V	1.0	2.2	-			
			N-ch, V _{DS} = 0.5V	V _{IN} =2.0V	3.0	7.7	-	mA	3	
Output Current (Standard Voltage)		Іоит		V _{IN} =3.0V	5. 0	10.1	-			
				V _{IN} =4.0V	6.0	11.5	-			
(2.0	(Claridara Voltage)		-	V _{IN} =5.0V	7.0	13.0	_ 747	512	274	
			CMOS, P-ch, V _{DS} =2.1V	V _{IN} =8.0V		-10.0	-2.0	ZSC.C	4	
Leakage	CMOS		V _{IN} =6.0V, V _{OUT} =6.0V ^{*1} V _{IN} =10.0V, V _{OUT} =10.0V ^{*2}		74	10	-	nA 3		
Current	N-ch Open Drain	I _{LEAK}			-	10	100		3	
Tempe Ch <mark>arac</mark>	erature teristics	$\Delta V_{DF}/$ $(\Delta Topr \cdot V_{DF})$	-40°C ≦ Topr ≦ 85°C		-	±100	-	ppm/	1	
D <mark>elay Ti</mark> me (VDR → Vo∪τ inversion)		t _{DLY}	Vdr→Vout inve	ersion	-	0.03	0.2	ms	5	

NOTE:

VDF (T): Nominal detect voltage Release Voltage: VDR = VDF + VHYS

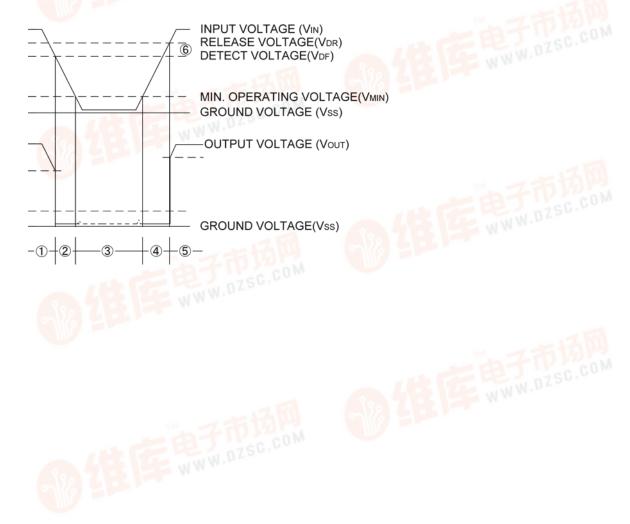


■OPERATIONAL EXPLANATION

CMOS output

- (Nout) When input voltage (VIN) rises above detect voltage (VDF), output voltage (VOUT) will be equal to VIN. (A condition of high impedance exists with N-ch open drain output configurations.)
- ② When input voltage (VIN) falls below detect voltage (VDF), output voltage (VOUT) will be equal to the ground voltage (VSS) level.
- (Vin) falls to a level below that of the minimum operating voltage (VMIN), output will become unstable. (As for the N-ch open drain product of XC61CN, the pull-up voltage goes out at the output voltage.)
- When input voltage (VIN) rises above the ground voltage (Vss) level, output will be unstable at levels below the minimum operating voltage (VMIN). Between the VMIN and detect release voltage (VDR) levels, the ground voltage (Vss) level will be maintained.
- (VDR), output voltage (VOIT) will be equal to VIN. (A condition of high impedance exists with N-ch open drain output configurations.)
- 6 The difference between VDR and VDF represents the hysteresis range.

Timing Chart





■NOTES ON USE

- 1. Please use this IC within the stated absolute maximum ratings. For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded.
- 2. When a resistor is connected between the VIN pin and the power supply with CMOS output configurations, oscillation may occur as a result of voltage drops at RIN if load current (IOUT) exists. (refer to the Oscillation Description (1) below)
- 3. When a resistor is connected between the V_{IN} pin and the power supply with CMOS output configurations, irrespective of N-ch open-drain output configurations, oscillation may occur as a result of through current at the time of voltage release even If load current (lout) does not exist. (refer to the Oscillation Description (2) below)
- 4. Please use N-ch open drain output configuration, when a resistor R_{IN} is connected between the V_{IN} pin and power source. In such cases, please ensure that RIN is less than $10k\Omega$ and that C is more than 0.1μ F, please test with the actual device. (refer to the Oscillation Description (1) below)
- 5. With a resistor RIN connected between the VIN pin and the power supply, the VIN pin voltage will be getting lower than the power supply voltage as a result of the IC's supply current flowing through the V_{IN} pin.
- 6. In order to stabilize the IC's operations, please ensure that V_{IN} pin input frequency's rise and fall times are more than 2 μ s/ V.
- 7. Torex places an importance on improving our products and its reliability. However, by any possibility, we would request user fail-safe design and post-aging treatment on system or equipment.

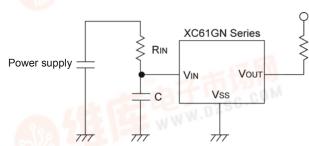


Figure 1: Circuit using an input resistor

Oscillation Description

(1) Load current oscillation with the CMOS output configuration

When the voltage applied at power supply, release operations commence and the detector's output voltage increases. Load current (IOUT) will flow at RL. Because a voltage drop (RIN x IOUT) is produced at the RIN resistor, located between the power supply and the Vin pin, the load current will flow via the IC's Vin pin. The voltage drop will also lead to a fall in the voltage level at the VIN pin. When the VIN pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at RIN will disappear, the voltage level at the VIN pin will rise and release operations will begin over again.

Oscillation may occur with this "release - detect - release" repetition.

Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current

Since the XC61G series are CMOS IC s, through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, oscillation is liable to occur as a result of drops in voltage at the through current's resistor (RIN) during release voltage operations. (refer to Figure 3)

Since hysteresis exists during detect operations, oscillation is unlikely to occur.

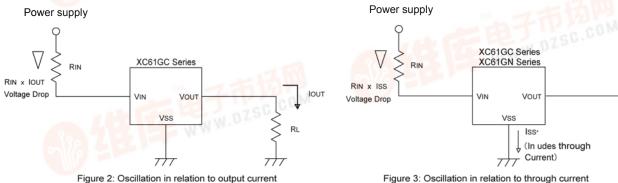


Figure 3: Oscillation in relation to through current



TEST CIRCUITS

Circuit 2 Circuit 1 100 kΩ (* 1) VIN VIN VIN Vout VOUT Vss Vss WWW.DZSO.GO1 Circuit 4 Circuit 3 VIN VIN Vout VOUT Vss Vss Circuit 5 R $\begin{cases}
100 k\Omega \\ (*1)
\end{cases}$ VIN measurement VOUT waveform Vss

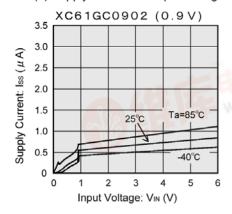
* 1: The resistor is not necessary with CMOS output products.

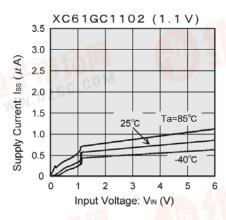


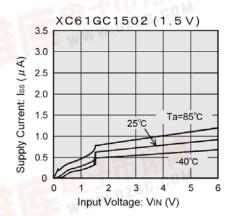
■TYPICAL PERFORMANCE CHARACTERISTICS

Low Voltage

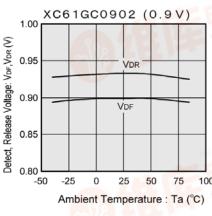
(1) Supply Current vs. Input Voltage

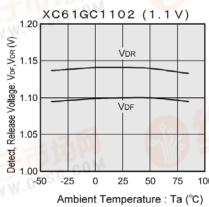


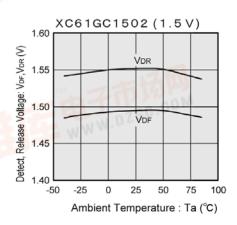




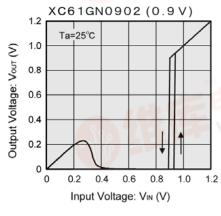
(2) Detect, Release Voltage vs. Ambient Temperature

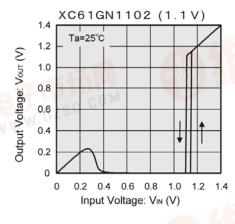


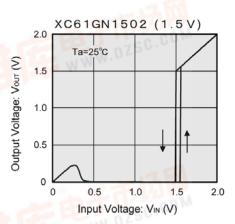




(3) Output Voltage vs. Input Voltage







Note: Unless otherwise stated, the N-ch open drain pull-up resistance value is $100k\Omega$.

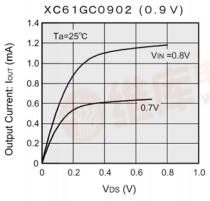


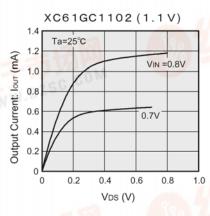
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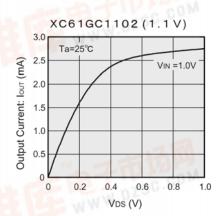
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

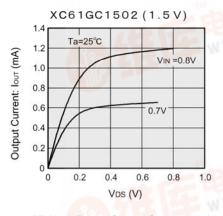
■Low Voltage (Continued)

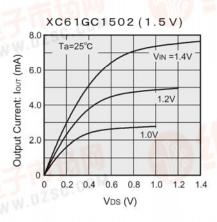




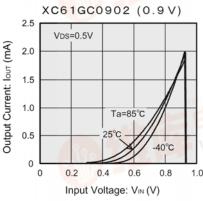


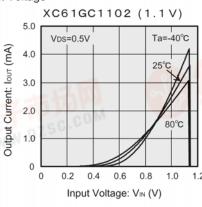


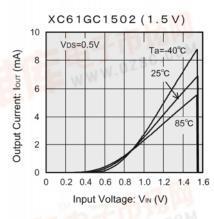




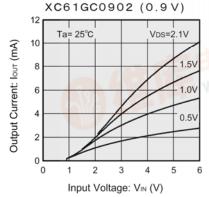
(5) N-ch Driver Output Current vs. Input Voltage

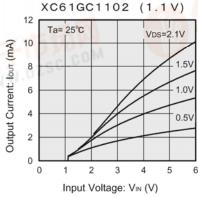


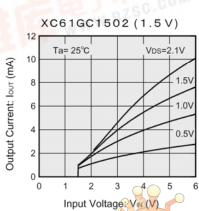




(6) P-ch Driver Output Current vs. Input Voltage

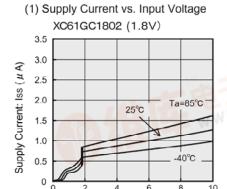




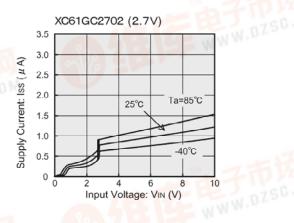


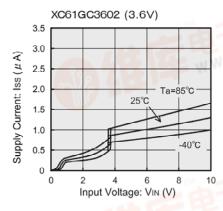
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

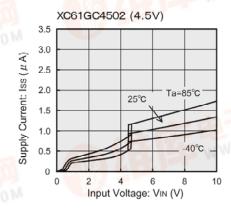
Standard Voltage



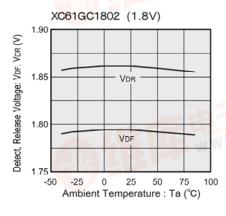
Input Voltage: Vin (V)

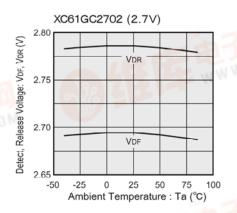


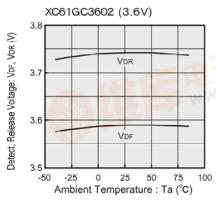


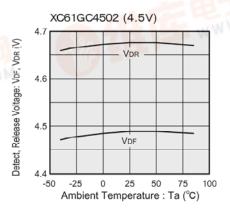


(2) Detect, Release Voltage vs. Ambient Temperature









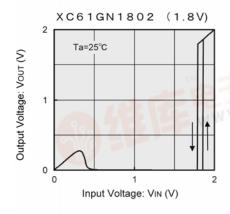


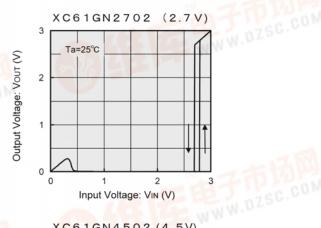
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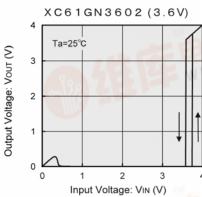
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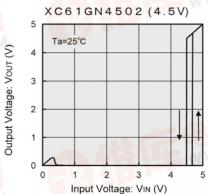
Standard Voltage (Continued)

(3) Output Voltage vs. Input Voltage



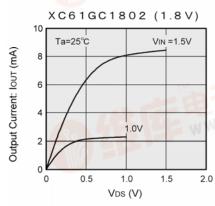


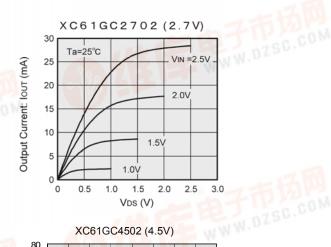


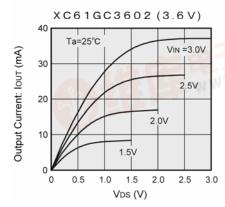


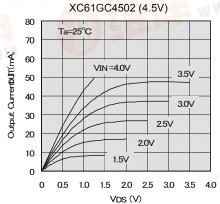
Note: Unless otherwise stated, the N-ch open drain pull-up resistance value is $100k\Omega$.











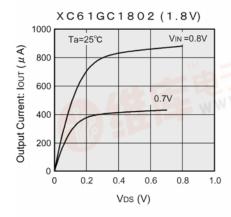
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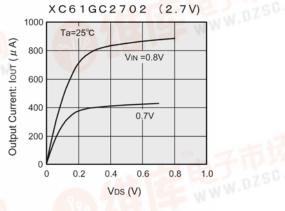
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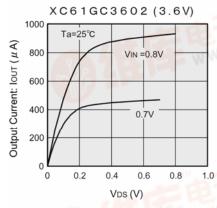
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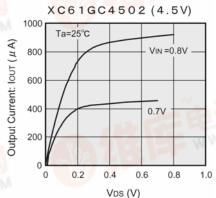
Standard Voltage (Continued)

(4) N-ch Driver Output Current vs. Vps

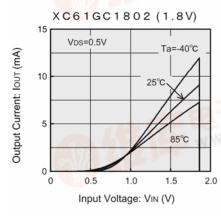


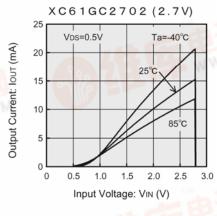


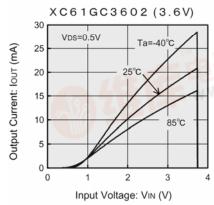


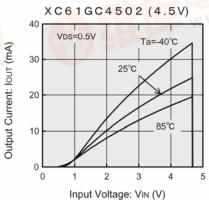


(5) N-ch Driver Output Current vs. Input Voltage







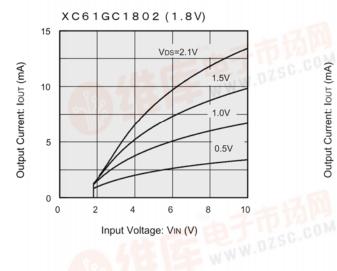


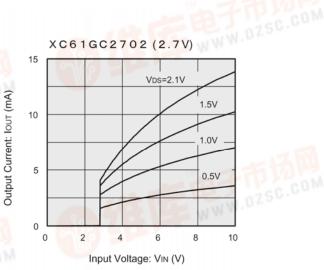
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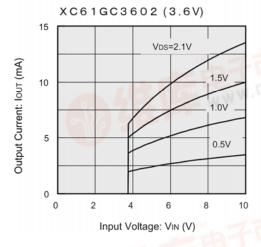
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

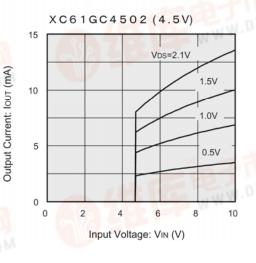
Standard Voltage (Continued)

(6) P-ch Driver Output Current vs. Input Voltage







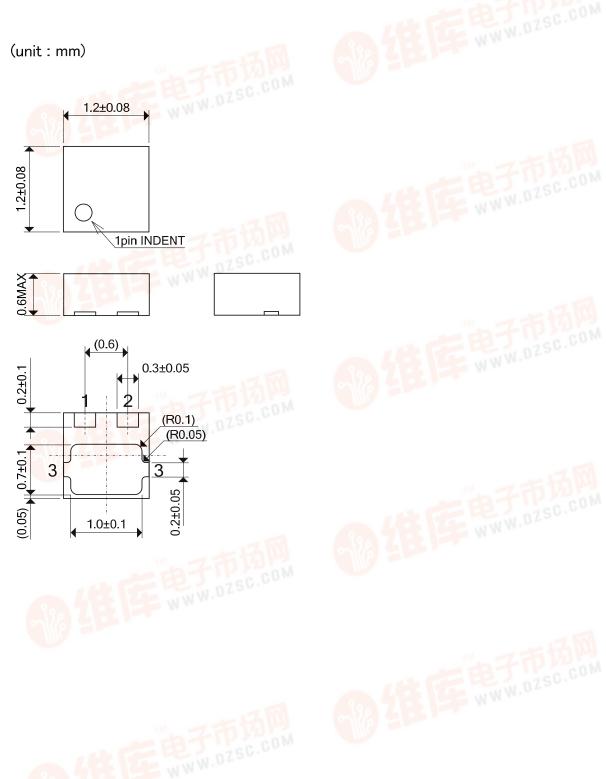






■ PACKAGING INFORMATION

●USP-3



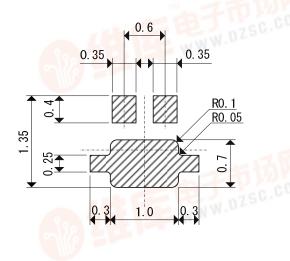


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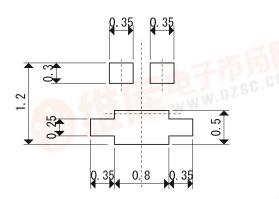
■ PACKAGING INFORMATION (Continued)

●USP-3

Reference Pattern Layout Dimension



Reference metal mask design





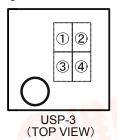






■MARKING RULE

●USP-3



① represents integer of output voltage and detect voltage CMOS Output (XC61GC series)

CONFIGURATION	VOLTAGE (V)
CMOS	0.x
CMOS	1.x
CMOS	2.x
CMOS	3.x
CMOS	4.x
CMOS	5.x
CMOS	6.x
	CMOS CMOS CMOS CMOS CMOS CMOS

N-ch Open Drain Output (XC61GN series)

MARK	CONFIGURATION	VOLTAGE (V)
K	N-ch	0.x
L L	N-ch	1.x
M	N-ch	2.x
N	N-ch	3.x
1.0750 P	N-ch	5.x
R	N-ch	6.x
S	N-ch	7.x

2 represents decimal number of detect voltage

MARK	VOLTAGE (V)	MARK	VOLTAGE (V)
0	x.0	5	x.5
1	x.1	6	x.6
2	x.2	7	x.7
3	x.3	8	x.8
4	x.4	9	x.9

3 based on internal standards

MARK	
3	

④ represents production lot number 0 to 9, A to Z repeated (G, I, J, O, Q, W excluded)



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